

Rev.E Mar.-2016

WR0<5 M M E QSQ Æ M ı s ll 1 Silicon NPN transistor in a TO-92 Plastic Package.

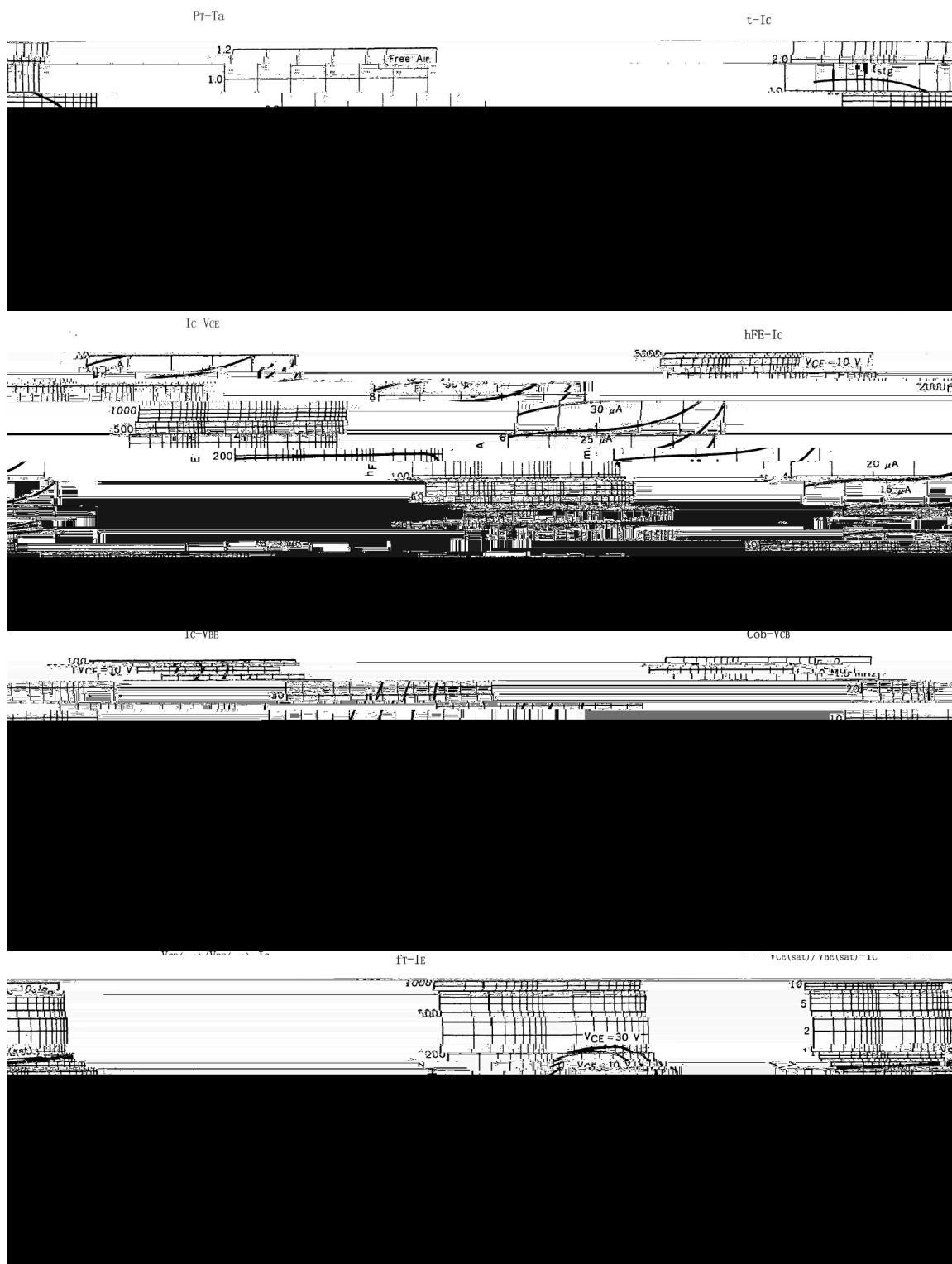
с с я і ѿ з і о Б/лб 5VD46:9 Ы ´

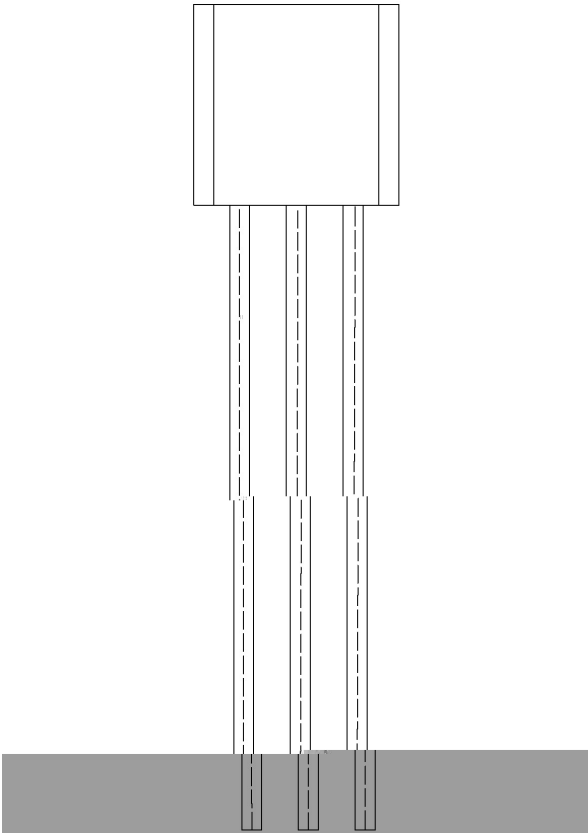
High breakdown voltage, good h_{FE} linearity, complementary to 2SA1376.

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General purpose amplifier applications requiring high breakdown voltages.

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	200	V
Collector to Emitter Voltage	V_{CEO}	180	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current - Continuous	I_C	100	mA
Collector Current – Continuous(Pulse)	I_{CP}	200	mA
Base Current - Continuous	I_B	20	mA
Collector Power Dissipation	P_C	750	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T		





Б " X

EU: ƛ 3 " Γb

F67: ; X ƛ 3 " Γb

0= ƛ k_{1H} ' 6 Γb

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Note:

BR: Company Code.

C3478: Product Type.

0= h



б " χ

- 1 ǀ 𐀀 𐀁 25 𐀂 150 𐀃 𐀄 𐀅 𐀆 60 𐀇 90sec;
- 2 Š Œ 𐀈 𐀉 255 ° 5 𐀊 𐀋 𐀌 𐀍 𐀎 𐀏 𐀐 5 ° 0.5sec;
- 3 𐀑 𐀒 𐀓 𐀔 𐀕 𐀖 𐀗 𐀘 2 𐀙 10 𐀚 /sec.

Note:

- 1.Preheating:25~150 𐀃 , Time:60~90sec.
- 2.Peak Temp.:255 ° 5 𐀊 , Duration:5 ° 0.5sec.
3. Cooling Speed: 2~10 𐀚 /sec.

𐀁 𐀂 χ 270 ° 5 𐀃 𐀄 𐀅 χ 10 ° 1 sec. Temp:270±5 Time:10±1 sec

𐀆 𐀇 𐀈 𐀉 / BULK

Package Type	Units	Dimension	(unit mm3)
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